

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes TFTs designed in accordance with characteristics of circuits. In a first structure of the invention, the TFT is formed by using a crystalline silicon film made of a unique crystal structure body. The crystal structure body has a structure in which rod-like or flattened rod-like crystals grow in a direction parallel to each other. In a second structure of the invention, growth distances of lateral growth regions are made different from each other in accordance with channel lengths of the TFTs. By this, characteristics of TFTs formed in one lateral growth region can be made as uniform as possible.